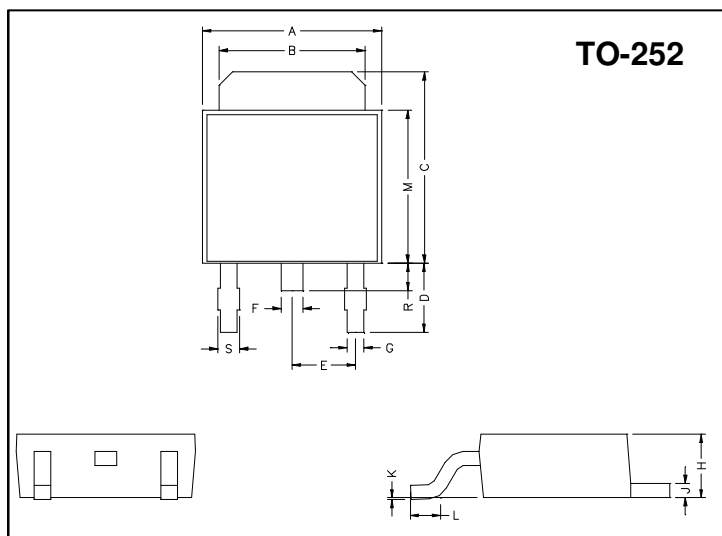
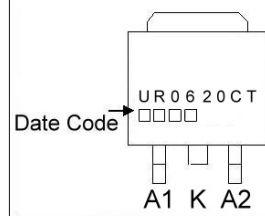
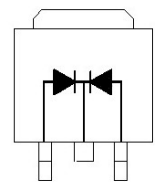


GJUR0620CT**SUPER FAST RECOVERY RECTIFIER****VOLTAGE 200V, CURRENT 6A****Description**

The GJUR0620CT consists of two super fast recovery rectifier diodes with common Cathodes.

Features

- *Glass passivated chip junctions
- *Low power loss
- *Low forward voltage, high current capability
- *High surge current capability
- *Super fast recovery times for high efficiency
- *High temperature soldering guaranteed: 260°C/10 seconds at terminals

Package Dimensions**Marking :****Diagram :**

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.20	2.80	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Operating and Storage Temperature	Tj, Tstg	-55 ~ +150	°C
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	200	V
Maximum RMS Voltage	V _{RMS}	140	V
Maximum DC Blocking Voltage	V _{DC}	200	V
Maximum Average Forward Rectified Current	I _O	6	A
Peak Forward Surge Current 8.3ms single half sine-wave Superimposed on rated load (JEDEC method)	I _{FSM}	100	A
Typical Junction Capacitance per leg ¹	C _J	30	pF
Typical thermal resistance ²	R _{θJC}	5.0	°C/W
Total Power Dissipation	P _D		mW

Electrical Characteristics at Ta = 25°C

Characteristic	Symbol	Min.	Max.	Unit	Test Conditions
Forward Voltage	V _F	-	0.975	V	I _F =3A
Reverse Breakdown	V _R	200	-	V	I _R =100uA
Reverse Current at rated DC blocking voltage per leg	I _R TC=25°C	-	5	uA	V _R =200V
	I _R TC=100°C	-	150		
Reverse Recovery Time per leg	t _{rr}	-	35	ns	I _F =0.5A, I _r =-1.0A, I _{rr} =-0.25A

Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 4.0 volts.

2. Thermal resistance from junction to case per leg mounted on heatsink.

Characteristics Curve

FIG. 1 - TYPICAL FORWARD CURRENT DERATING CURVE

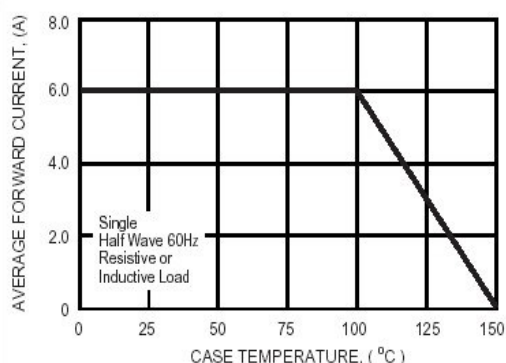


FIG. 2 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

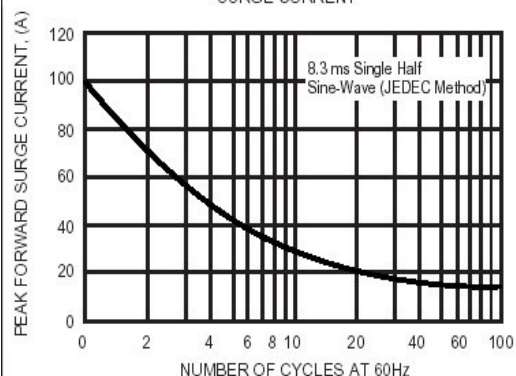


FIG. 3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

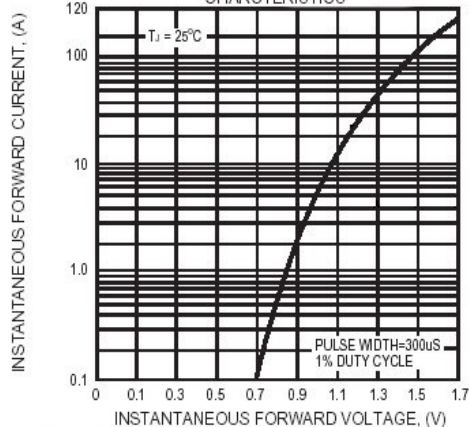


FIG. 4 - TYPICAL REVERSE CHARACTERISTICS

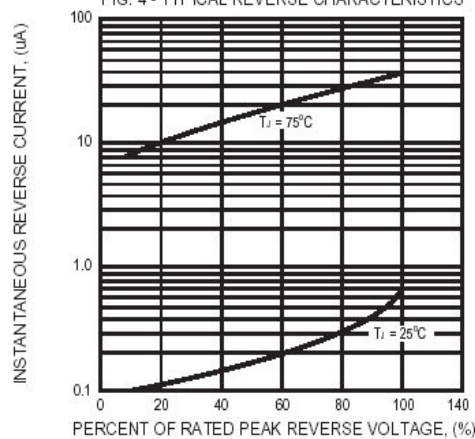
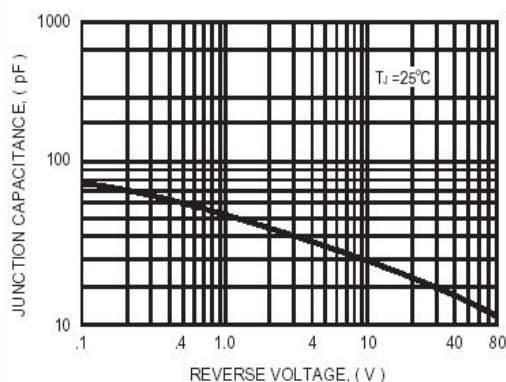


FIG. 5 - TYPICAL JUNCTION CAPACITANCE



Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165